



METAL OXIDE SEMICONDUCTOR (MOS) BANDGAP VOLTAGE
REFERENCE CIRCUIT

Inventor: Paul David Ranucci

Application No.: 10/730,201

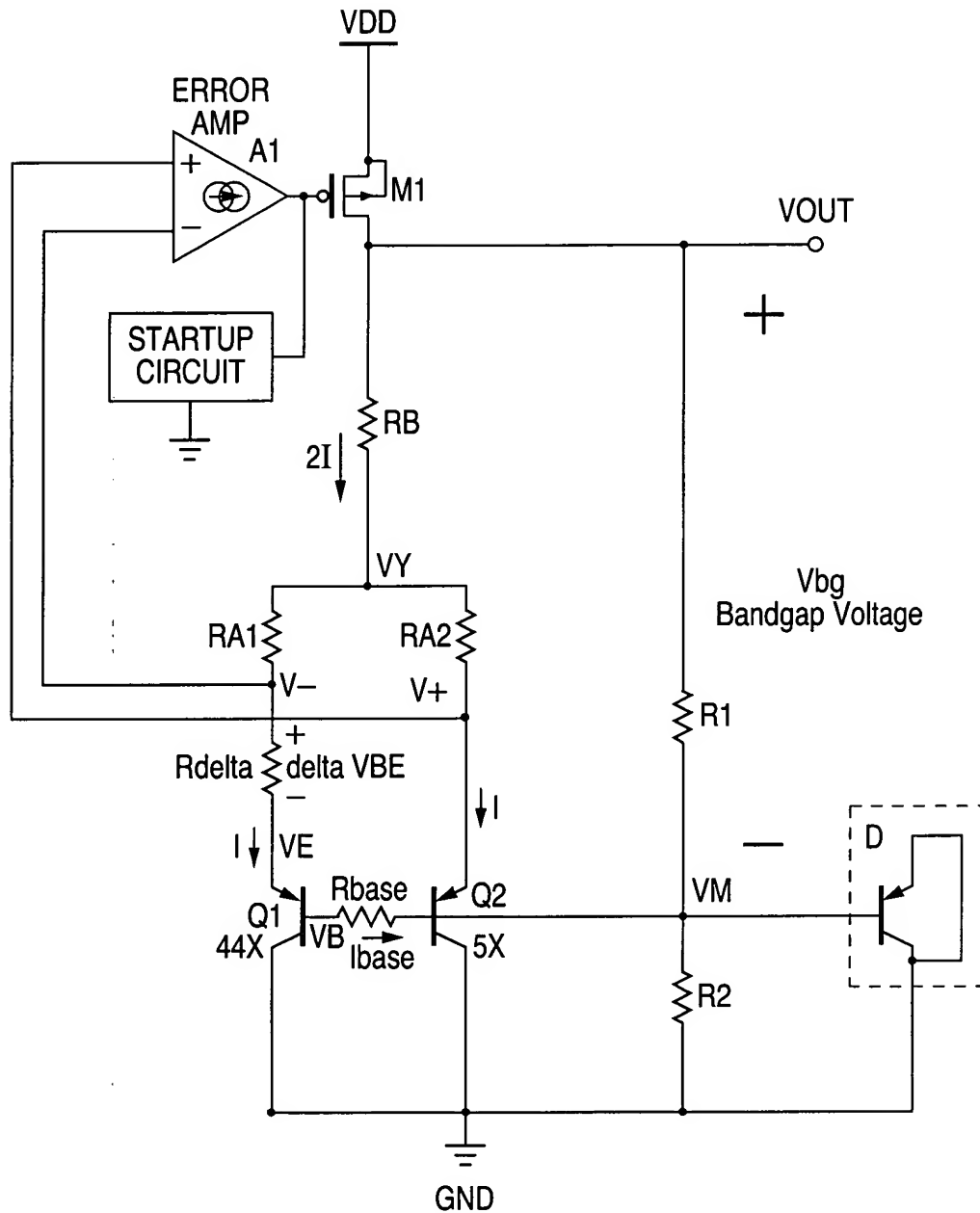


FIG. 1

METAL OXIDE SEMICONDUCTOR (MOS) BANDGAP VOLTAGE
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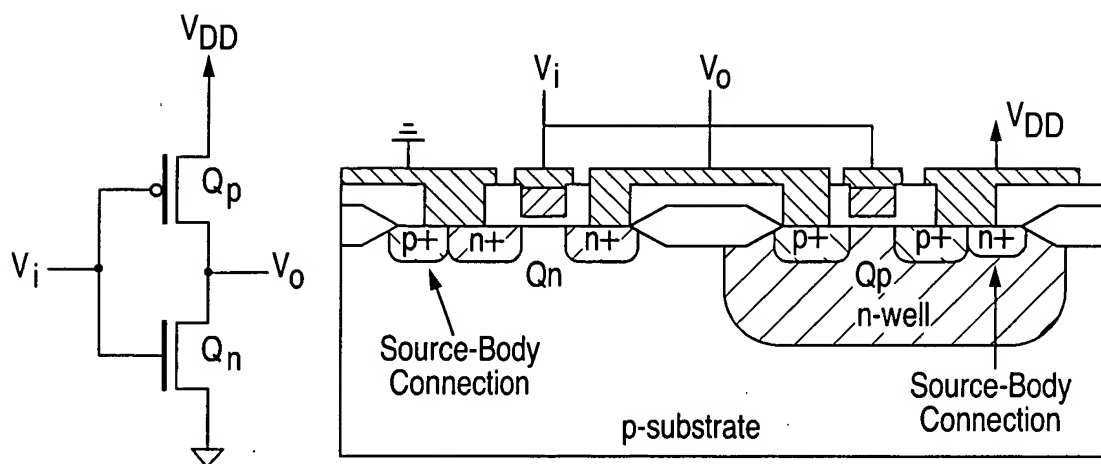


FIG. 1A

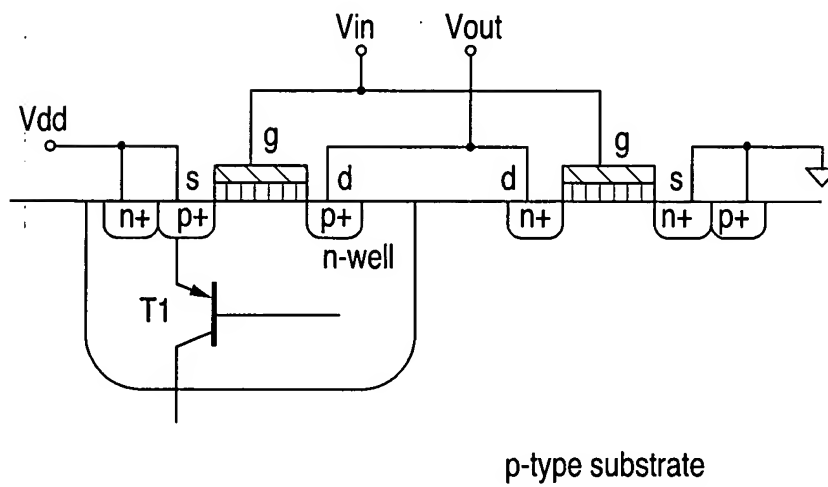


FIG. 1B

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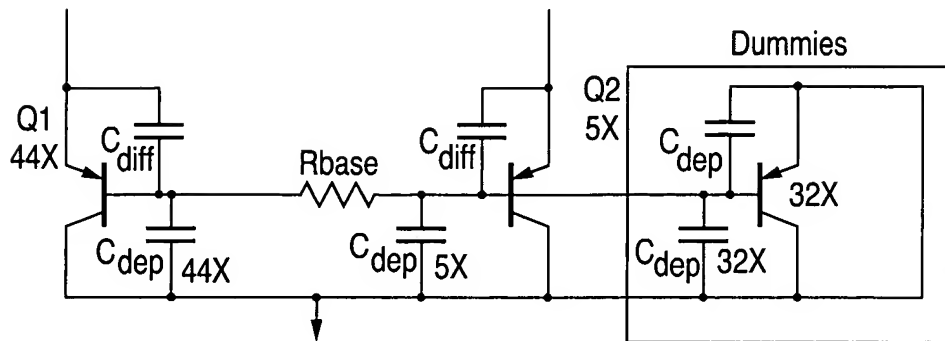


FIG. 2

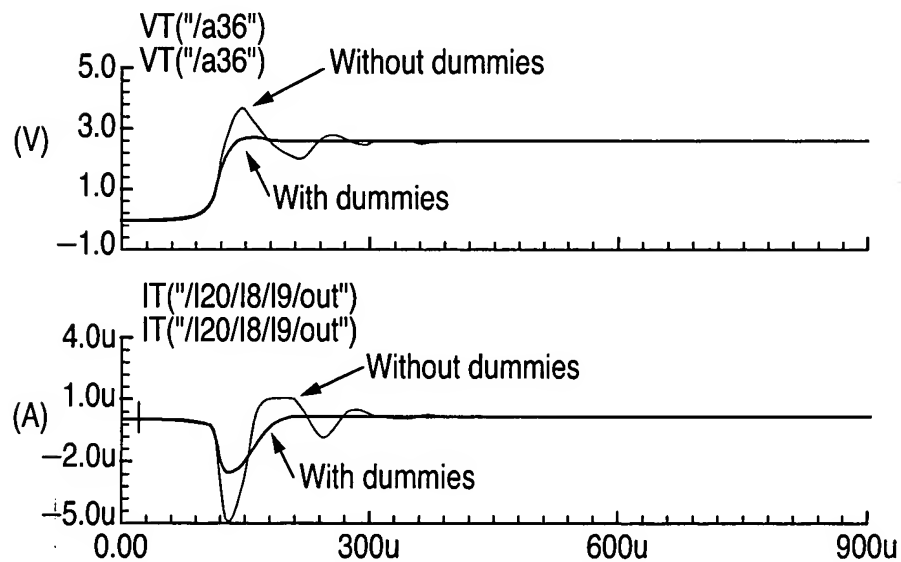


FIG. 4

METAL OXIDE SEMICONDUCTOR (MOS) BANDGAP VOLTAGE
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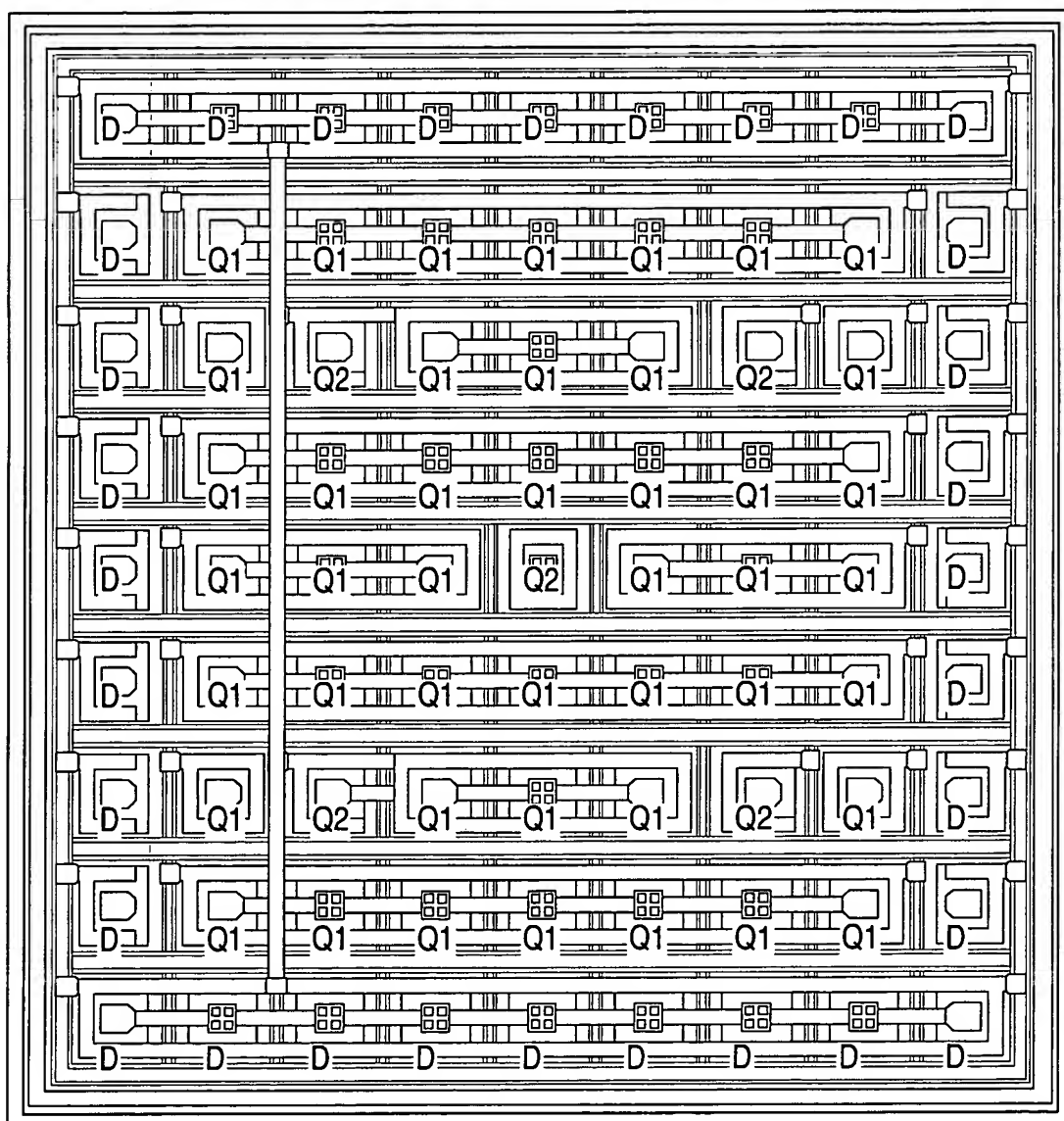


FIG. 3